

In The Claims:

1. (original) A programming method of the multi-level flash memory, comprising:
shooting a programming voltage that is increasing upwards stepwise each time into a gate of the multi-level flash memory to change a state of the multi-level flash memory; and
shooting an additional programming voltage into the multi-level flash memory after the last programming voltage is shot when a highest value of the multi-level is being programmed in the multi-level flash memory.

2. (original) The method of claim 1, wherein the programming method can be used in a binary flash memory.

3. (original) A programming method of the multi-level flash memory, comprising:
shooting a programming voltage that is increasing upward stepwise each time into a gate of the multi-level flash memory to change a sate of the multi-level flash memory; and
shooting an additional programming voltage into the multi-level flash memory after the last programming voltage is shot when a value of the multi-level is being programmed in the multi-level flash memory.

4. (original) The method of claim 3, wherein the programming method can be used in a binary flash memory.

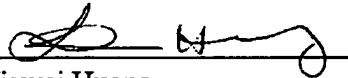
Claim 5. (canceled)

No new matter has been added to the application by the amendments made to the claims.

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Correspondence Address:
4 Venture, Suite 250
Irvine, CA. 92618
Tel.: (949) 660-0761

Respectfully submitted,
J.C. PATENTS

By: 
Jiawei Huang
Registration No. 43,330